

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2752

DESCRIPTION

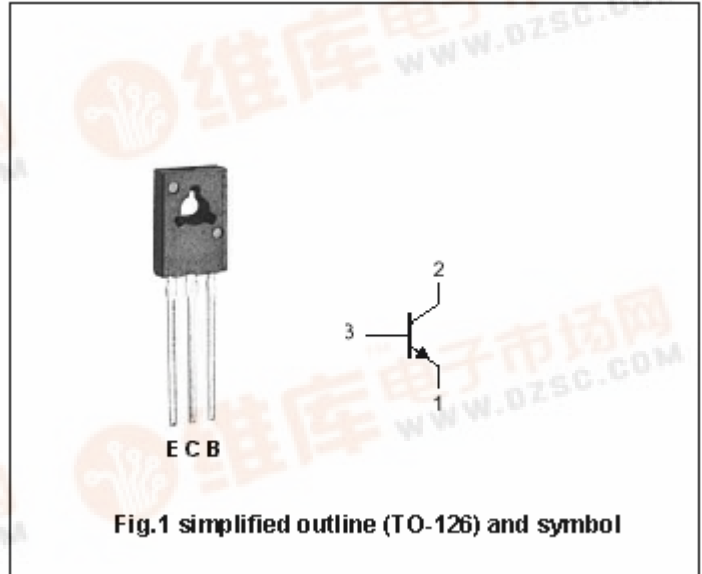
- With TO-126 package
- High breakdown voltage
- Low collector saturation voltage

APPLICATIONS

- Low power switching regulator
- DC-DC converter
- High voltage switch

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		0.5	A
I _{CM}	Collector current-peak		1.0	A
I _B	Base current		0.25	A
P _C	Collector power dissipation	T _a =25	1.0	W
		T _C =25	10	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.3A; I _{B1} =0.06A, L=10mH	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =300mA; I _B =60mA			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =300mA; I _B =60mA			1.2	V
I _{CEX}	Collector cut-off current	V _{CE} =400V; V _{BE} =-1.5V T _C =125			0.01 1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =50mA; V _{CE} =5V	20		80	
h _{FE-2}	DC current gain	I _C =300mA; V _{CE} =5V	10			

Switching times

t _{on}	Turn-on time				1.0	μs
t _{stg}	Storage time	I _C =300mA; I _{B1} =-I _{B2} =60mA PW 50 μs; V _{CC} 150V R _L =500			2.5	μs
t _f	Fall time				1.0	μs

◆ h_{FE-1} Classifications

M	L	K
20-40	30-60	40-80

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PACKAGE OUTLINE

